Method for fabricating a semiconductor structure including a metal oxide interface with silicon

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Abstract of **TW 468212 (B)**

A method of fabricating a semiconductor structure including the steps of providing a silicon substrate (10) having a surface (12), forming on the surface (12) of the silicon substrate (10), by atomic layer deposition (ALD), a seed layer (20; 20') comprising a silicate material and forming, by atomic layer deposition (ALD) one or more layers of a high dielectric constant oxide (40) on the seed layer (20; 20').

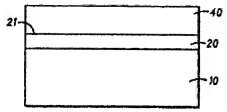

FIG. 9